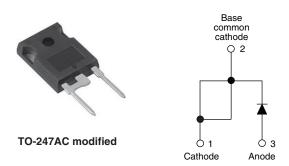


Hyperfast Rectifier, 30 A FRED Pt®



PRIMARY CHARACTERISTICS						
30 A						
600 V						
1.34 V						
See Recovery table						
175 °C						
TO-247AC modified						
Single						

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Single diode device
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test









ROHS COMPLIANT HALOGEN FREE

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

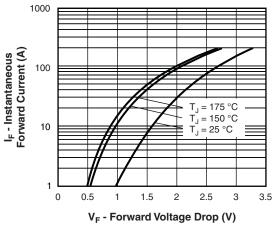
ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V_{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 116 °C	30	۸			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	300	A			
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-			
Forward voltage	V _F	I _F = 30 A	-	2.0	2.6	V		
		I _F = 30 A, T _J = 150 °C	-	1.34	1.75			
Develope legicome eviment		$V_R = V_R$ rated	-	0.3	50			
Reverse leakage current	I _R	T _J = 150 °C, V _R = V _R rated	-	60	500	μΑ		
Junction capacitance	C _T	V _R = 600 V	-	33	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	3.5	-	nH		

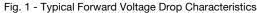


DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, dI_F/dt =$	50 A/μs, V _R = 30 V	-	28	35			
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	31	-	ns		
		T _J = 125 °C		-	77	-			
Peak recovery current	I _{RRM}	T _J = 25 °C		-	3.5	-	۸		
		T _J = 125 °C		-	7.7	-	A		
Reverse recovery charge	0	T _J = 25 °C		-	65	-	0		
	Q _{rr}	T _J = 125 °C		-	345	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	BOL TEST CONDITIONS		TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction to case per leg	R _{thJC}		-	0.5	0.9			
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.4	-			
Weight			-	6.0	-	g		
vveignt			-	0.22	-	OZ.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-247AC modified		30EPH06H				



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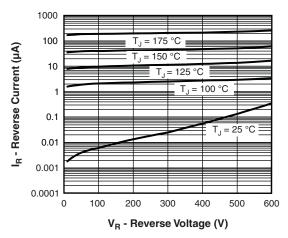


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

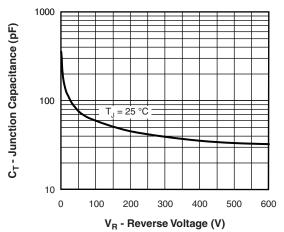


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

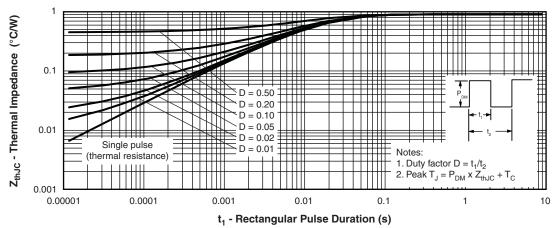


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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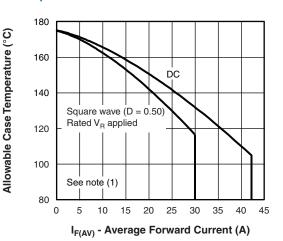


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

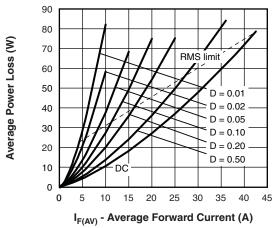


Fig. 6 - Forward Power Loss Characteristics

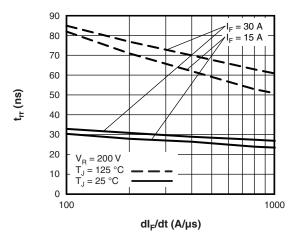


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

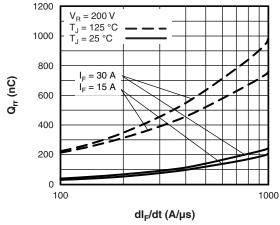


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R

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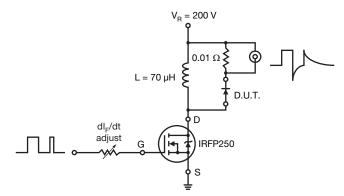
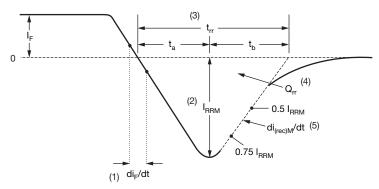


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

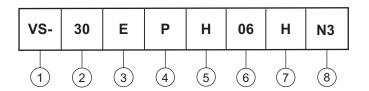
(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (30 = 30 A)

3 - Circuit configuration:

E = single diode

4 - Package:

P = TO-247AC modified

5 - H = hyperfast recovery

6 - Voltage rating (06 = 600 V)

7 - H = AEC-Q101 qualified

8 - Environmental digit:

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

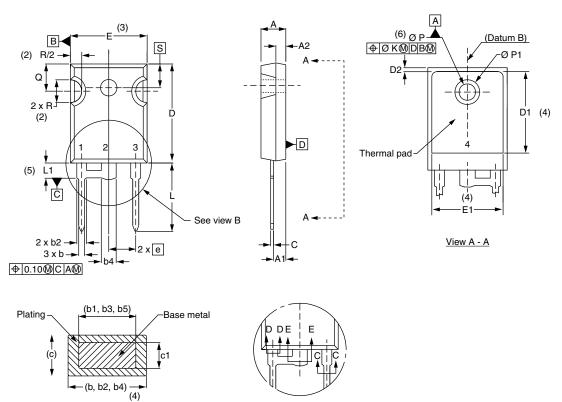
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-30EPH06HN3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95253</u>					
Part marking information	www.vishay.com/doc?95442				
SPICE model	www.vishay.com/doc?96573				



TO-247AC modified

DIMENSIONS in millimeters and inches



View B

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

Section C - C, D - D, E - E

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.530	-	
е	5.46	BSC	0.215	BSC	
ØK	0.254		0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	ı	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c



Vishay

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